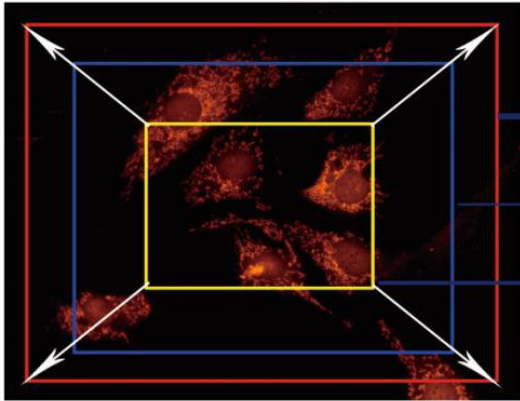


1.2 inch——Wider field of view

1.2 inch sensor with larger lighting area to offer better imaging performance and full view of specimen.



1.2 inch
1 inch
2/3 inch

Specification

Item	MSH12-BI	A/D convert	12bit
Effective resolution	4.2 Megapixels	Trigger mode	Software trigger
Sensor size	1.2 inch	Image cache	128Mb
Pixel size	6.5 μ m \times 6.5 μ m	Cooling mode	Peltier cooling mode, room temperature -15 $^{\circ}$ C
Frame rate	2048 \times 2048 22fps	Exposure	Manual exposure / Auto exposure / Zone exposure
	2048 \times 1500 29fps	Image format	TIF, BMP, JPG, RAW
	Any size of ROI	Software	DirectShow / TWAIN
Scanning mode	Progress scan/Continuous output	OS system	Windows XP 32bit; Windows 7/8/10 32/64bit;
Shutter type	Rolling Shutter	Data port	USB3.0 B type, 5Gb/s
Exposure time	22 μ s - 120s	Camera port	C-mount adapter
Effective gain	1x - 16x	Surrounding	Work temperature 0~50 $^{\circ}$ C, Work humidity 10%~85%RH
Spectral response	200 - 1100nm	Dimension	\varnothing 113.2 \times 105 \times 92.6mm

Guangzhou Micro-shot Optical Technology Co. Ltd

Add: Room 506 Building A 1933 Huaguan Road / Tianhe District, Guangzhou / 510640 China
www.m-shot.com / sales@m-shot.com / TEL:0086-20-38262481



Mshot

MSH12-BI

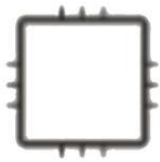
Back lighting sCMOS camera



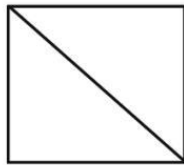
Brief introduction

MSH12-BI a research level back lighting sCMOS camera achieves perfect balance of high resolution and high sensitivity, maximize the detection of signals, also it combines the ability of high speed and wide dynamic range, it can be widely used in materials and life science, such as low light imaging, fluorescence imaging, spectral imaging and other fields.

Technical advantages



Scientific CMOS
Monochrome sensor



1.2 " big sensor



2.0e-read out noise
Super low noise



30000e- large
Full-well capacity



-15° peltier cooling
Low dark current control

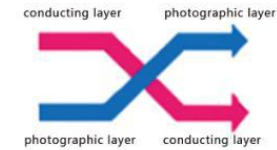
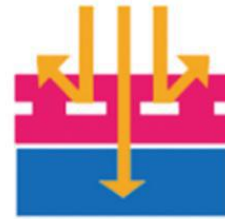


High speed USB3.0
Rapid and stable

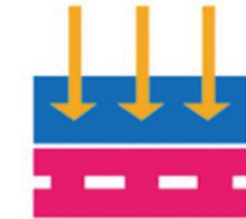
Back lighting CMOS sensor technology

Traditional front lighting structure sensor, the photodiode is located behind the circuit transistor, the amount of incoming light will be affected by occlusion, the sensitivity becomes smaller and weaker. While MSH12-BI uses back lighting CMOS, the sensor with backlight structure moves the sensitive layer over the conductive layer to change the traditional structure, the whole photosensitive layer is more sensitive to the incident light, obtaining better brightness, noise control and sensitivity.

Traditional CMOS



Back lighting CMOS



High sensitivity

Quantum efficiency is the probability that photons can be converted into photoelectrons at a certain wavelength, which is related to the wavelength. The quantum efficiency of MSH12-BI has been greatly improved, the quantum efficiency is 95% at wavelength 560nm.

